



#### **Product Summary**

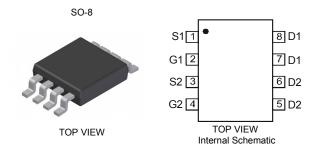
V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	40mΩ @ V <sub>GS</sub> = -4.5V	-5.8A
	$70$ m $\Omega$ @ V <sub>GS</sub> = -2.5V	-4.4A

#### Description

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Backlighting
- **Power Management Functions**
- DC-DC Converters

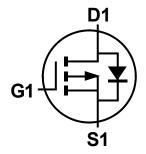


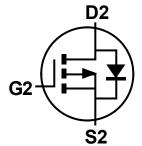
#### **Features**

- **Dual P-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections Indicator: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (approximate)





P-Channel MOSFET

P-Channel MOSFET

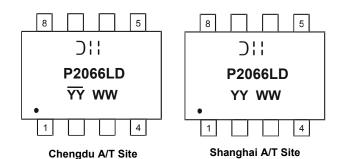
#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2066LSD-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



⊃¦¦ = Manufacturer's Marking P2066LD = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 14 = 2014) WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±12	V	
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-5.8 -4.6	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-20	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

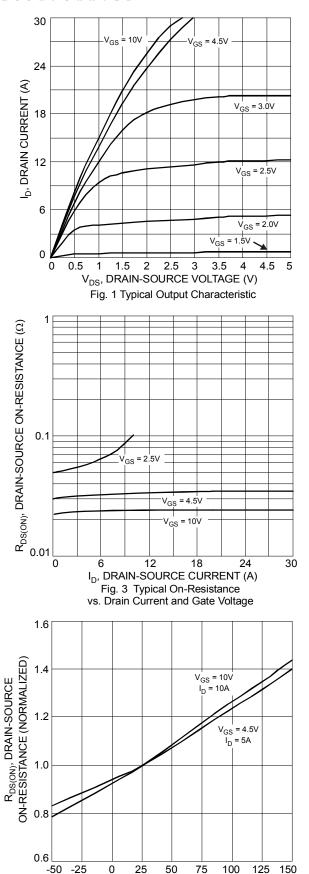
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Observatoristis	0	Min	T	M	1114	T4 O	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	1		1	1		1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.6	-0.94	-1.2	V	$V_{DS} = V_{GS}$ , $I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	_	_	29	40		$V_{GS} = -4.5V$ , $I_D = -4.6A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	55	70	mΩ	$V_{GS} = -2.5V$ , $I_D = -3.8A$	
Forward Transconductance	9fs	_	9	_	S	$V_{DS} = -10V$ , $I_D = -4.6A$	
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-0.5	-0.72	-1.4	V	$V_{GS} = 0V$ , $I_S = -2.1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>	_	820	_	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V — f = 1.0MHz	
Output Capacitance	Coss	_	200	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	160	_	pF	-1 - 1.0ivii iz	
Gate Resistance	R <sub>G</sub>	_	2.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS	<u>.</u>			•			
Total Gate Charge	$Q_{G}$	_	10.1	_			
Gate-Source Charge	Q <sub>GS</sub>	_	1.5	_	nC	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $I_{D} = -5.9A$	
Gate-Drain Charge	$Q_GD$	_	4.3	_		ID = -3.9A	
Turn-On Delay Time	t <sub>d(on)</sub>		4.4	_		V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,	
Rise Time	t <sub>r</sub>		9.9	_	ne		
Turn-Off Delay Time	t <sub>d(off)</sub>	_	28.0	_	ns	$I_D = -1A$ , $R_G = 6.0\Omega$	
Fall Time	t <sub>f</sub>	_	23.4	_			

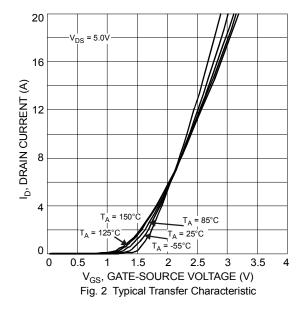
5. Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB. 6. Pulse width  $\leq$ 10 $\mu$ S, Duty Cycle  $\leq$ 1%. Notes:

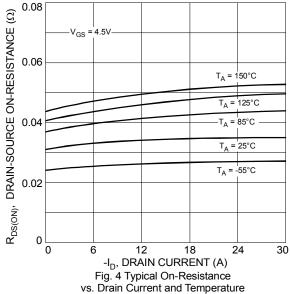
7. Short duration pulse test used to minimize self-heating effect.





T<sub>A</sub>, AMBIENT TEMPERATURE (°C)
Fig. 5 Normalized On-Resistance vs. Ambient Temperature





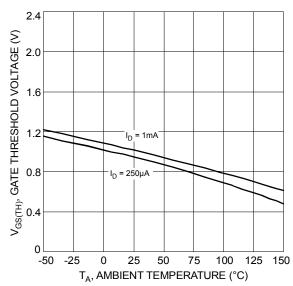
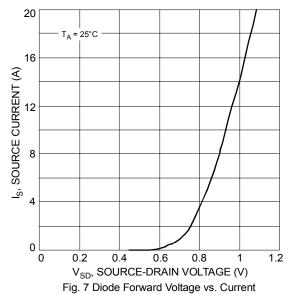
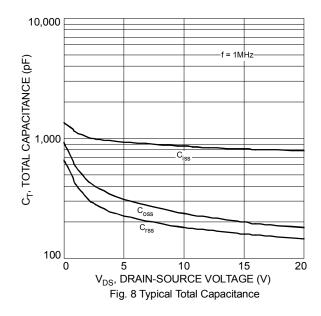


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

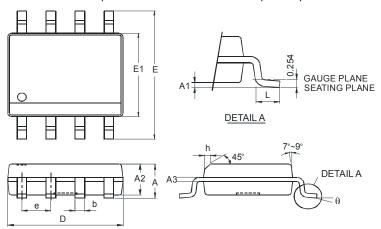






## **Package Outline Dimensions**

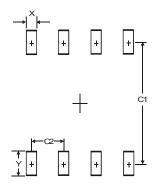
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	1	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
E	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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